

**REMARKS**

Applicants hereby cancel claim 11 in order to more completely set forth the scope of the invention.

In response to the rejection of claims 10 and 12-18 under 35 U.S.C. 112, second paragraph, applicant responds as follows:

The amendment of claims 10 and 18 should traverse the above rejection.

In response to the rejection of claims 10 and 12-18 under 35 U.S.C. 102(b), the applicant responds as follows:

The novel features of the amended claims 10 and 18 reside in a) the first multiple semiconductor layers of the first semiconductor laser structure are made of III-V compound, and the V element is one selected from the group consisting As and P, while the second multiple semiconductor layers of the second semiconductor laser structure are made of III-V compound, and the V element is another selected from the group consisting As and P, b) the etching control layer is provided between the first semiconductor laser structure and the substrate but not provided between the second semiconductor laser structure and the substrate, and c) the composition of the etching control layer is different from the composition of the first multiple semiconductor layers and the composition of the substrate.

Accordingly, since during the forming of the first semiconductor laser structure by etching, the etching can be stopped at the etching control layer, the substrate provided below the etching control layer will not be damaged.

On the other hand, cited reference Treati et al. (hereafter Treati) merely teaches a structure in which two semiconductor laser devices having the same AlGaInP cladding layer (c) are formed on a substrate (see column 5, line 58 – column 6, line 53, and Fig.4). According to Treati, since the two semiconductor laser devices have the same AlGaInP cladding layer (c), it is not possible forming the first semiconductor laser structure by etching. Hence, Treati fails to disclose the function of an etching control layer.

Moreover, according to the amended claims 10 and 18, the composition of the first multiple semiconductor layers of the first semiconductor laser structure and that of the second multiple semiconductor layers of the second semiconductor laser structure are different, while the composition of the two semiconductor laser devices in Treati is the same.

Even though Treati teaches two semiconductor laser devices, it is expected that neither of them is formed by etching.

For the foregoing reasons, since Treati fails to disclose that the composition of the first multiple semiconductor layers of the first semiconductor laser structure and that of the second multiple semiconductor layers of the second semiconductor laser structure are different, the etching control layer is provided between the first semiconductor laser structure and the substrate but not provided between the second semiconductor laser structure and the substrate, and the composition of the etching control layer is different from the composition of the first multiple semiconductor layers and the composition of the substrate, the amended claims 10 and 18 are patentable over Treati.

Further, since the amended claim 10 is patentable over Treati, dependent claims 12-17 are also patentable.

Examination on the merits is respectfully requested.

If a conference would expedite prosecution of the instant application, the Examiner is hereby invited to telephone the undersigned to arrange such a conference.

Respectfully submitted,



Donald R. Studebaker  
Registration No. 32,815

NIXON PEABODY LLP  
401 9<sup>th</sup> Street, N.W.  
Suite 900  
Washington, D.C. 20004-2128  
(202) 585-8000